



GBJ25005 - GBJ2510/G

Single Phase 25Amp Glass passivated Bridge Rectifiers

Features

- · Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0
- The G suffix is uses for photoresist chip, otherwise it is a knife scraping chip

MECHANICAL DATA

- Case: Molded plastic, GBJ
- Terminals: Plated Leads Solderable perMIL-STD-202, Method 208
- Polarity: As Marked on Case
- Mounting Position: Any
- Marking: Type Number
- · Lead Free: For RoHS / Lead Free Version

Maximum Ratings And Electrical Characteristics (@T_A=25°C unless otherwise noted)

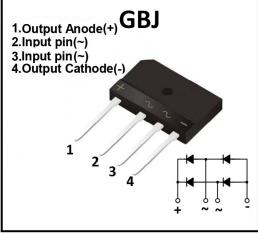
Symbol	Parameter	GBJ	GBJ	GBJ	GBJ	GBJ	GBJ	GBJ	Unit	
		25005	2501	2502	2504	2506	2508	2510		
V _{RRM}	repetitive peak reverse voltage	50	100	200	400	600	800	1000		
V _{RWM}	Working Peak Reverse Voltage	50	100	200	400	600	800	1000	V	
V _{RMS}	RMS voltage	35 70 140 280 420		560	700					
V _{DC}	DC blocking voltage	50	100	200	400	600	800	1000	1	
IF _{AV}	Average Rectified Output	25.0							A	
	Current (Note 1)@T _C =90°C	25.0								
I _{FSM}	Peak forward surge current, 8.3ms single	300						A		
	half sine-wave									
l ²	I ² _t Rating for fusing (t<8.3ms)	373.50					A _S ²			
V _{FM}	Forward Voltage @IF=12.5A	1.0						V		
	per element @IF=25A	1.10								
	Peak Reverse Current@T _A =25°C	5.0					uA			
I _R	at rated DC blocking voltage @T _A =125 $^{\circ}$ C	500								
CJ	Typical junction capacitance	85					pF			
R _{θJA}	Between junction and ambient, Without heatsink	22					°C/W			
$R_{ ext{ heta}JC}$	Between junction and case, With heatsink	1.0								
TJ	Operation Temperature Range	-55 to +150					°C			
T _{STG}	Storage Temperature Range	-55 to +150								
		1							1	

Note:(1)Thermal resistance from junction to case per element. Unit mounted on 75x75x1.6mm aluminum plate heat sink. BORN SEMICONDUCTOR , INC. ALL

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Mechanical Data







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Ratings And Characteristic Curves

Figure 1: Output Current Derating Curve

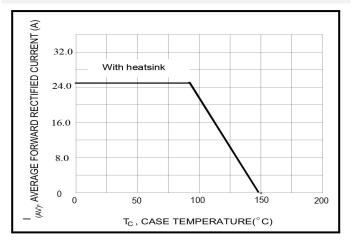


Figure 3:Maximum Peak Forward Surge Current (per

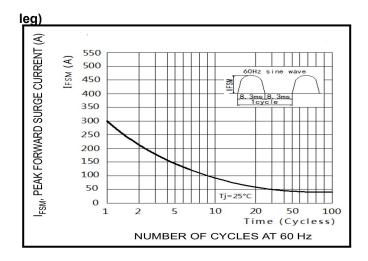
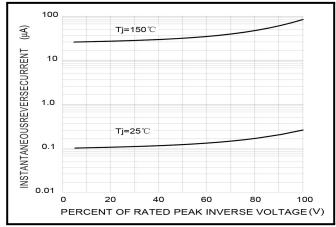


Figure 5:TYPICAL REVERSE CHARACTERISTICS



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Figure 2: Typical Forward Characteristics (per leg)

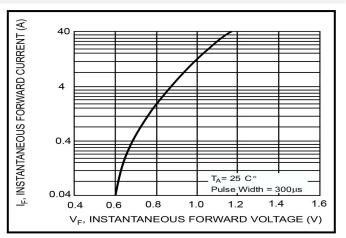
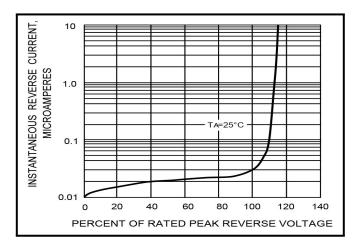


Figure 4: Typical Junction Capacitance





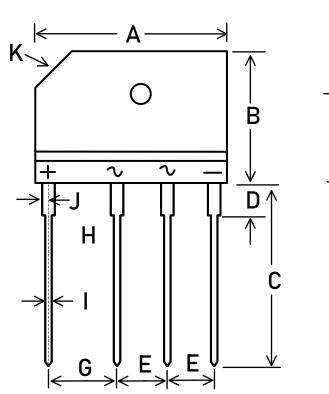




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Outline Drawing -GBJ



-S→	L ⊨÷	M ▶ ↓ ↓ N
_	~	← P
R	 → ←	

CVMDOL	MILLIMETER				
SYMBOL	MIN.	MAX.			
А	29.70	30.3			
В	19.70	20.3			
С	17.00	18.00			
D	3.80	4.20			
E	7.30	7.70			
G	9.80	10.20			
Н	2.00	2.40			
I	0.90	1.10			
J	2.30	2.70			
K	3.0x	κ45°			
L	4.40	4.80			
М	3.40	3.80			
N	3.10	3.40			
Р	2.50	2.90			
R	0.60	0.80			
S	10.80	11.20			

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Specifications are subject to change without notice. Please refer to http://www.born-tw.com for current information. Revision: 2022-Jan-1

